

Description

The AO3400-ED uses advanced trench technology

to provide excellent R_{DS(ON)}, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

D G SOT-23

General Features

 $V_{DS} = 20V I_{D} = 3A$

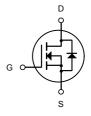
 $R_{DS(ON)} < 55 m\Omega @ V_{GS} = 4.5 V$

Application

Battery protection

Load switch

Uninterruptible power supply



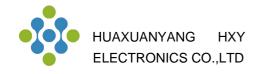
N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AO3400-ED	SOT-23	A09T	3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	20	V
V _G s	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous	3	А
Ідм	Drain Current-Pulsed (Note 1)	12	A
P _D	Maximum Power Dissipation	0.9	W
ТЈ,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	139	°C/W



Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20	22	-	V
Zero Gate Voltage Drain Current	Ipss	V _{DS} =20V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	Igss	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _G S(th)	V _{DS} =V _{GS} ,I _D =250µA	0.5	0.75	1.2	V
		V _{GS} =2.5V, I _D =2A	-	62	73	mΩ
Drain-Source On-State Resistance	RDS(ON)	R _{DS(ON)} V _{GS} =4.5V, I _D =2.8A	-	43	55	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =3A	-	8	ī	S
Input Capacitance	C _{lss}		-	260	-	PF
Output Capacitance	Coss	V _{DS} =10V,V _{GS} =0V,	-	48	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	27	-	PF
Turn-on Delay Time	td(on)		-	2.5	-	nS
Turn-on Rise Time	t _r	V _{DD} =10V, R _L =3.3Ω	-	3.2	ī	nS
Turn-Off Delay Time	td(off)	V_{GS} =4.5V, R_{GEN} =6 Ω	-	21	-	nS
Turn-Off Fall Time	t _f		-	3	-	nS
Total Gate Charge	Qg		-	2.9	5	nC
Gate-Source Charge	Q _{gs}	V _{DS} =10V,I _D =3A,	-	0.4	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	0.6	-	nC
Diode Forward Voltage (Note 3)	VsD	V _{GS} =0V,I _S =3.3A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3.3	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

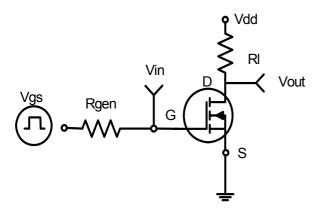


Figure 1:Switching Test Circuit

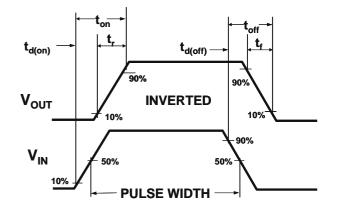


Figure 2:Switching Waveforms

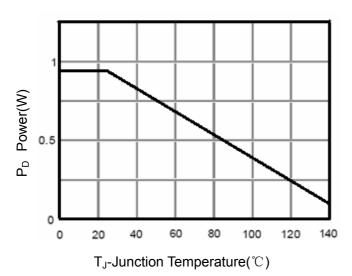


Figure 3 Power Dissipation

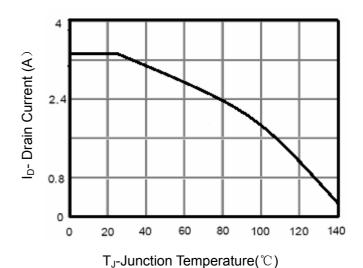


Figure 4 Drain Current

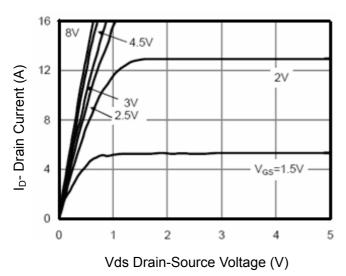


Figure 5 Output Characteristics

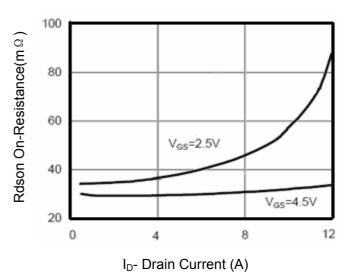


Figure 6 Drain-Source On-Resistance



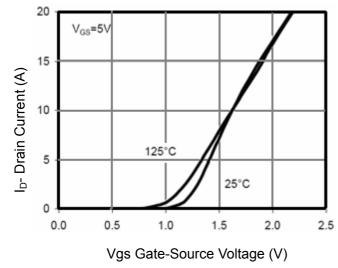
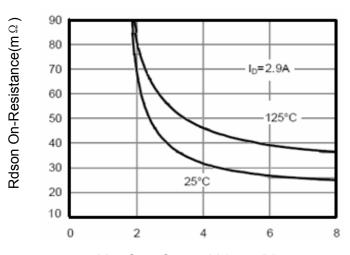


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

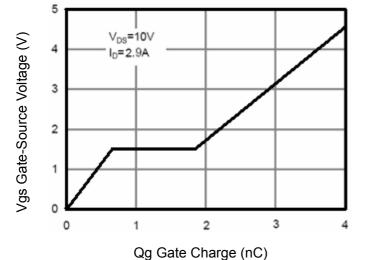
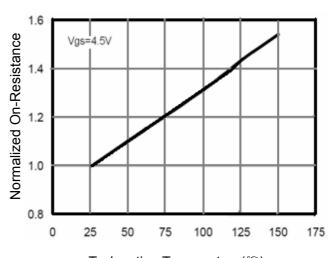


Figure 11 Gate Charge



 T_J -Junction Temperature(${}^{\circ}\mathbb{C}$)

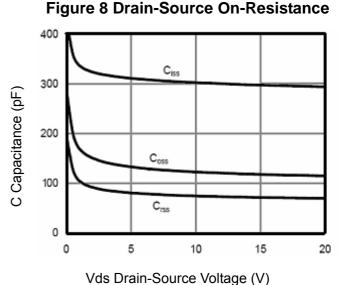
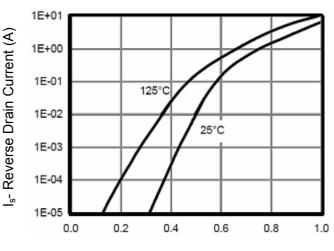


Figure 10 Capacitance vs Vds

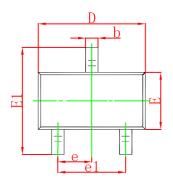


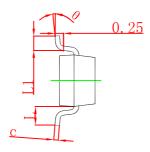
Vsd Source-Drain Voltage (V)

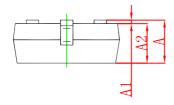
Figure 12 Source- Drain Diode Forward



SOT-23 Package Outline Dimensions

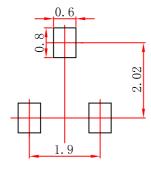






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibol	Min Max	Min	Max		
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	0 TYP 0.037 TYP		7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note:
 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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